INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	ATTY DOCKET NO. ITO.0544US (P15589)	SERIAL NO. 10/633,886
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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A.						
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	C.						
	D.						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
	E.							
	F.							
	G.							

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

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EXAMINER	Loke	DATE CONSIDERED	11/13/04

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.